High Voltage NPN Silicon Transistors

 \dots designed for medium to high voltage inverters, converters, regulators and switching circuits.

- High Collector–Emitter Voltage VCEO = 200 Volts
- DC Current Gain Specified @ 1.0 and 2.5 Adc
- Low Collector–Emitter Saturation Voltage VCE(sat) = 0.8 Vdc @ IC = 1.0 Adc

MAXIMUM RATINGS

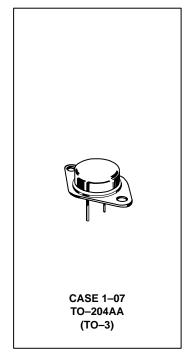
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	200	Vdc
Collector–Base Voltage	V _{CB}	200	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current — Continuous — Peak	lC	5.0 10	Adc
Base Current	ΙΒ	2.0	Adc
Total Device Dissipation @ T _C = 75°C Derate above 75°C	PD	100 1.33	Watts W/°C
Operating Junction Temperature Range	TJ	-65 to +150	°C
Storage Temperature Range	T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	0.75	°C/W

MJ410

5 AMPERE POWER TRANSISTOR NPN SILICON 200 VOLTS 100 WATTS



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (IC = 100 mAdc, IB = 0)	VCEO(sus)	200	_	Vdc
Collector Cutoff Current (V _{CE} = 200 Vdc, I _B = 0)	ICEO	_	0.25	mAdc
Collector Cutoff Current (V _{CB} = 200 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 125°C)	ICEX	_	0.5	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	IEBO	_	5.0	mAdc
ON CHARACTERISTICS	•			•
DC Current Gain ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 2.5 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	hFE	30 10	90 —	_
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)	VCE(sat)	_	0.8	Vdc
Base–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)	VBE(sat)	_	1.2	Vdc
DYNAMIC CHARACTERISTICS	•	-		•
Current–Gain — Bandwidth Product (IC = 200 mAdc, VCE = 10 Vdc, f = 1.0 MHz)	fT	2.5	_	MHz

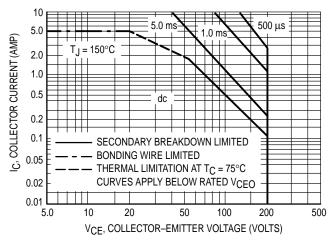


Figure 1. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Pulse curves are valid for duty cycles of 10% provided $T_{J(pk)} \le 150^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values than the limitations imposed by second breakdown.

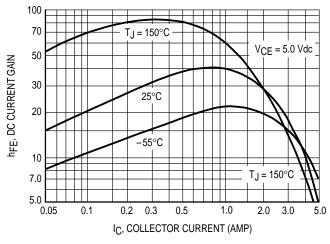


Figure 2. DC Current Gain

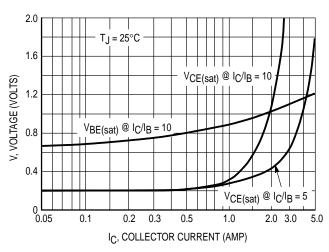


Figure 3. "On" Voltages

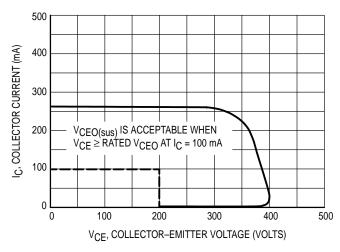


Figure 4. Sustaining Voltage Test Load Line

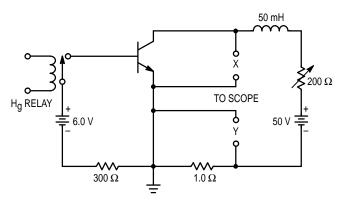
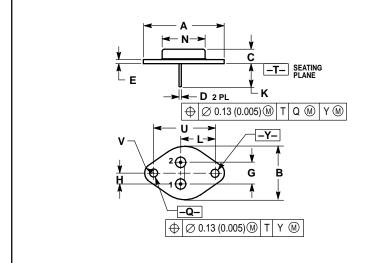


Figure 5. Sustaining Voltage Test Circuit

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	1.550 REF		39.37 REF			
В	-	1.050		26.67		
С	0.250	0.335	6.35	8.51		
D	0.038	0.043	0.97	1.09		
Е	0.055	0.070	1.40	1.77		
G	0.430 BSC		10.92 BSC			
Н	0.215	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19		
L	0.665 BSC		16.89 BSC			
N		0.830		21.08		
Q	0.151	0.165	3.84	4.19		
U	1.187 BSC 30.15 BS		BSC			
٧	0.131	0.188	3.33	4.77		

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

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